

HIGH VOLTAGE POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

PRELIMINARY Datasheet

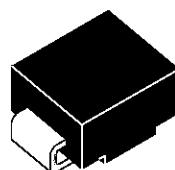
$I_{F(av)}$	1.5 A
V_{RRM}	100 V
V_F (max)	0.70 V

FEATURES AND BENEFITS

- NEGLIGIBLE SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP
- LOW CAPACITANCE
- HIGH REVERSE AVALANCHE SURGE CAPABILITY

DESCRIPTION

High voltage Schottky rectifier suited for SLIC protection during the card insertion operation.



SOD 6
(Plastic)

ABSOLUTE RATINGS(limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	100	V
$I_{F(RMS)}$	RMS Forward Current	10	A
$I_{F(AV)}$	Average Forward Current	$T_L = 90^\circ C$ $\delta = 0.5$ $V_R = 60V$	A
I_{FSM}	Surge Non Repetitive Forward Current	$tp = 10 \text{ ms}$ Sinusoidal	A
I_{RRM}	Peak Repetitive Reverse Current	$tp = 2 \mu s$ $F = 1 \text{ KHz}$	A
I_{RSR}	Non Repetitive Peak Reverse Current	$tp = 100 \mu s$	A
T_{stg}	Storage Temperature Range	-65 to +150	$^\circ C$
T_j	Max. Junction Temperature	115	$^\circ C$
dV/dt	Critical Rate of Rise of Reverse Voltage	1000	V/ μs

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R _{th} (j-l)	Junction-leads	20	°C/W

ELECTRICAL CHARACTERISTICS**STATIC CHARACTERISTICS**

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
V _F *	Forward Voltage Drop	T _j = 25°C	I _F = 100 mA			0.43	V
		T _j = 25°C	I _F = 3 A			0.95	
		T _j = 100°C	I _F = 1.5 A		0.57	0.71	
		T _j = 100°C	I _F = 3 A		0.67	0.85	
I _R **	Reverse Leakage Current	T _j = 25°C	V _R = V _{RRM}			30	µA
		T _j = 100°C			1	5	mA

Pulse test : * tp = 380 µs, duty cycle < 2 %

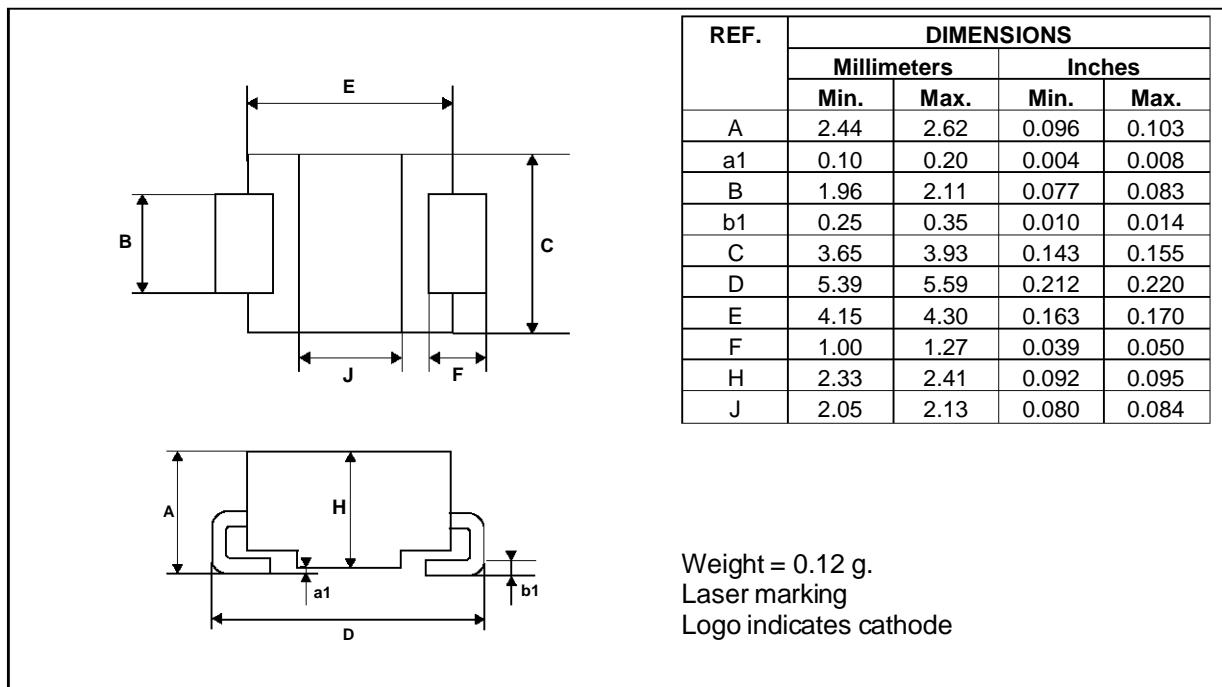
** tp = 5 ms, duty cycle < 2%

To evaluate the conduction losses use the following equation :

$$P = 0.65 \times I_{F(AV)} + 0.067 I_F^2 (\text{RMS})$$

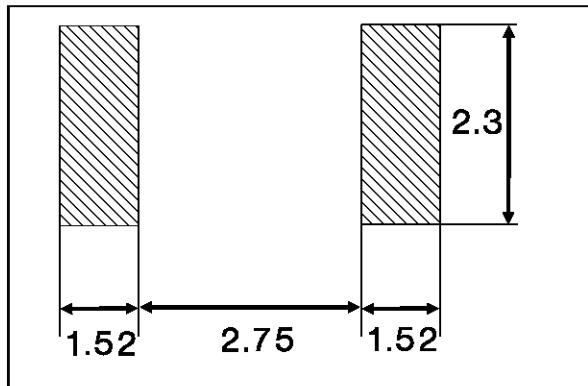
Typical junction capacitance, V_R = 0V F = 1MHz T_j = 25°C C = 365pF

PACKAGE MECHANICAL DATA
SOD 6 (Plastic)



FOOTPRINT DIMENSIONS (in millimeters)
SOD6 (Plastic)

Voltage (V)	100
Marking	E11



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